Glass and SIPOS Passivation High Voltage Diodes
玻璃与SIPOS钝化工艺高压二极管

■特征 Features

➢玻璃 SIPOS 钝化工艺芯片
Glass and SIPOS passivation chip
➢高反向电压
High Reverse Voltage
➢低反向漏电流
Low Reverse Leakage Current
➢塑封材料易燃性的 UL 94V-0 等级识别
Plastic material has UL flammability recognition 94V-0
➢符合 RoHS 要求
RoHS compliance
➢高温焊接保证：260℃±5℃/10 秒
High temperature soldering guaranteed: 260℃+5℃/10 seconds

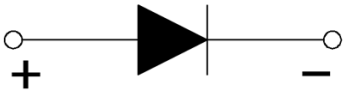
关键参数 KEY PARAMETERS		
参数 PARAMETER	数值 VALUE	单位 UNIT
$I_{F(AV)}$	350	mA
V_{RM}	12000	V
I_{FSM}	50	A
Package	-	

■应用范围 Applications

➢适用于“微波炉”高压整流
For high voltage rectification for“ MWO”

■机械参数 Mechanical Data

➢本体：塑封壳体
Case: Molded plastic case
➢终端：电镀引线可焊性每符合 MIL - STD - 750，方法 2026
Terminals: Plated leads solderable per MIL-STD-750, Method 2026
➢极性：管体标记
Polarity: Marked on Body
➢安装位置：任何
Mounting Position: Any
➢重量：约 2.5 克
Weight : About 2.5grams



■最大额定值 Maximum Ratings @ Ta = 25℃ unless otherwise noted

参数 PARAMETER		符号 Symbol	数值 Rating	单位 Unit
反向重复峰值电压 Repetitive Peak Reverse Voltage		V_{RM}	12000	V
平均正向电流 Average Forward Current	50Hz 正弦波负载,，Tc≤80℃ 50Hz sine wave load，Tc≤80℃	$I_{F（AV）}$	350	mA
最大正向浪涌电流 Peak Surge Forward Current	50Hz 正弦波, 1/2 周期，t=10ms, Tj=25℃ 50Hz sine wave, 1/2cycle , t=10ms, Tj=25℃	I_{FSM}	50	A
结温 Junction temperature		Tj	130	℃
存储温度 Storage temperature		T_{STG}	-40～130	℃

■电性特性 Electrical Characteristics @ Ta = 25℃ unless otherwise noted

参数 PARAMETER	测试条件 Test Conditions		符号 Symbol	数值 Rating	单位 Unit
正向峰值电压 Peak Forward Voltage	IF=350mA，脉冲测试 IF=350mA，Pulse measurement	Ta=25℃	VF	9 max	V
反向峰值电流 Peak Reverse Current	VR=VRM，脉冲测试，单个二极管的额定值 VR=VRM, Pulse measurement,Rating of per diode	Tj=25℃	IR	5 max	uA
		Tj=100℃		50 max	
反向击穿电压 Reverse Breakdown Voltage	IR=100uA	Tj=25℃	VZ	15 min	KV

■特性曲线 Characteristic Curve

FIG1.Derating Curve For Output Rectified Current

图 1. 电流降额曲线

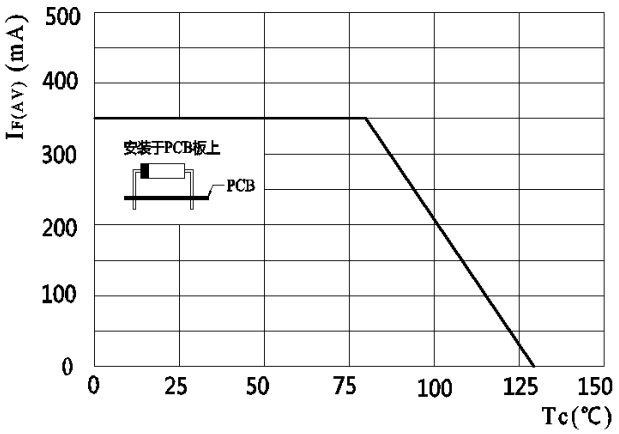


FIG2.Maximum Non-Repetitive Peak Forward Surge Current Per Bridge Element

图 2. 最大正向不重复峰值浪涌电流

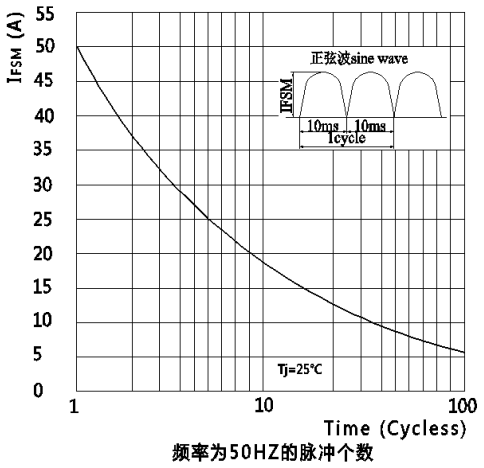


FIG3.Typical Reverse Characteristics Per Bridge Element

图 3. 典型反向特性

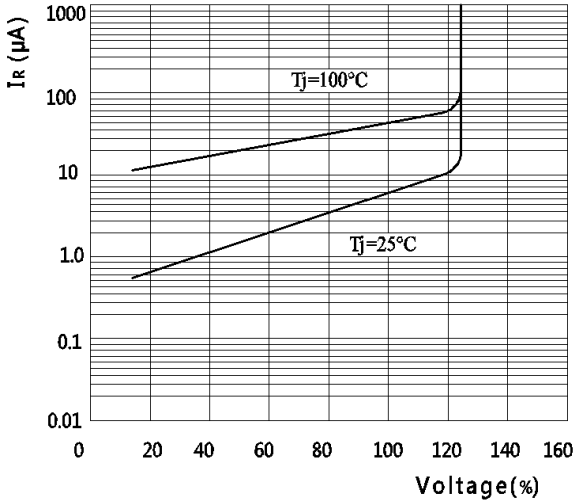
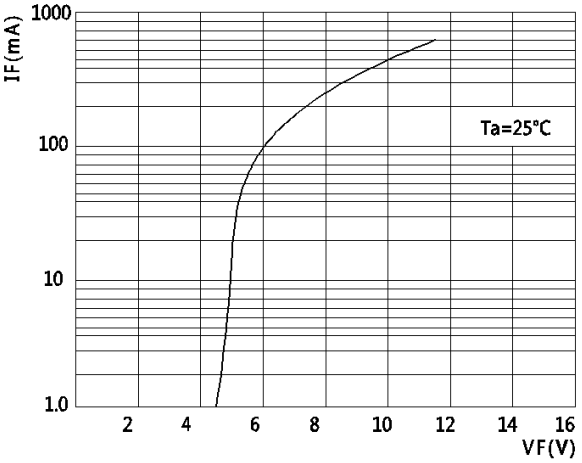
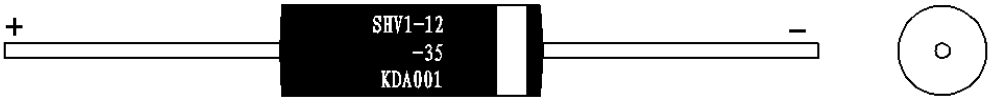


FIG4.Typical Forward Characteristics Per Bridge Element

图 4. 典型正向特性



■标记图 Marking Diagram

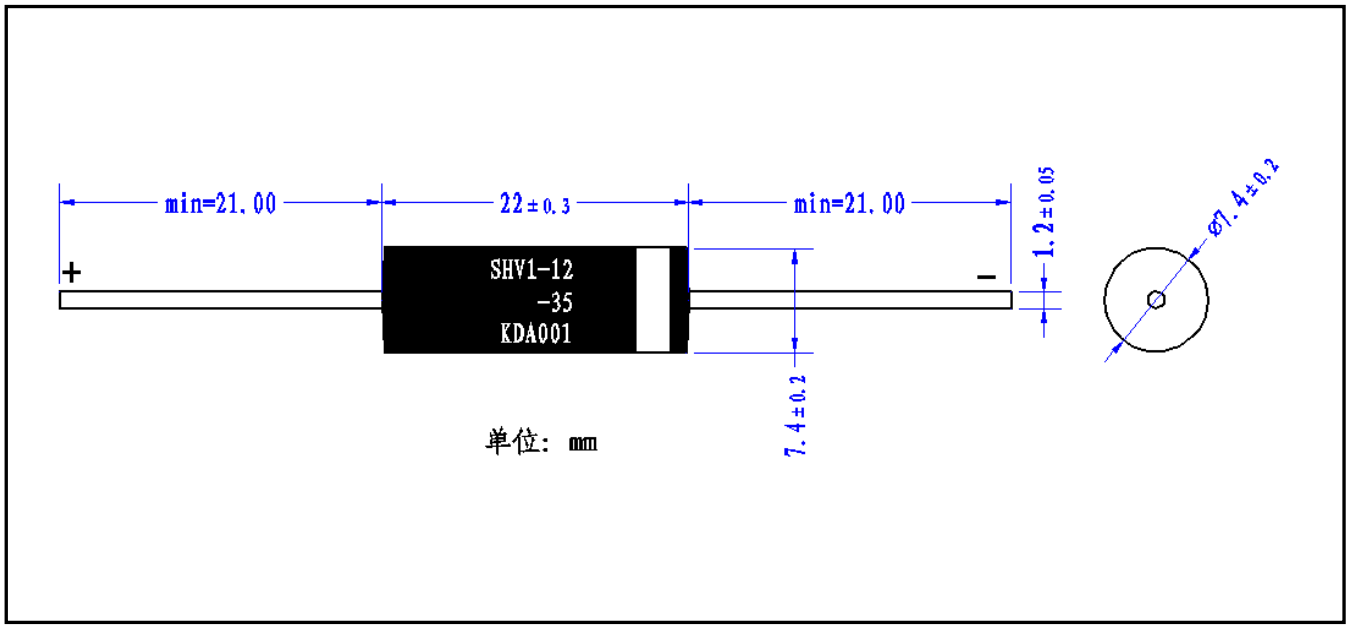


SHV1-12：（S：希尔）（HV：高压器件）（1：定频）（-12：12000V）

-35：额定电流350mA

KDA001：制程码（Process code）

■尺寸图 Dimension Drawing



其他要求：

可应客户要求加装 250/187 系列接线端子

We can set 250/187 terminal on the top of the wire, according to customer, s requirement.

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